

SEMICONDUCTOR STRUCTURE AND METHOD FOR MANUFACTURING THE SAME, AND MEMORY

ABSTRACT

Disclosed in embodiments of the present application are a semiconductor structure and a method for manufacturing the same, and a memory. The semiconductor structure comprises: a substrate, a plurality of oxide pillars, a plurality of active pillars, a first insulating layer and a storage structure. The plurality of oxide pillars are on the substrate and arranged in an array along a first direction and a second direction. Both the first direction and the second direction are parallel to a surface of the substrate, and the first direction intersects with the second direction. The first insulating layer is in a gap between the oxide pillars. Each active pillar is on a top surface of a corresponding one of the oxide pillars. The storage structure covers at least part of a side wall of the active pillar.

[Fig. 2]